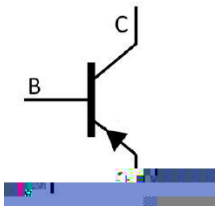
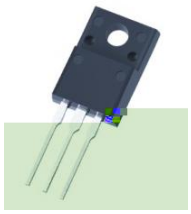
TO-220F PNP Silicon PNP transistor in a TO-220F Plastic Package.

Low saturation voltage, excellent dependence of h_{FE} on current, fast switching time.

Lamp drivers, power amplifiers, high-speed switching.





PIN1 Base PIN 2 Collector PIN 3 Emitter

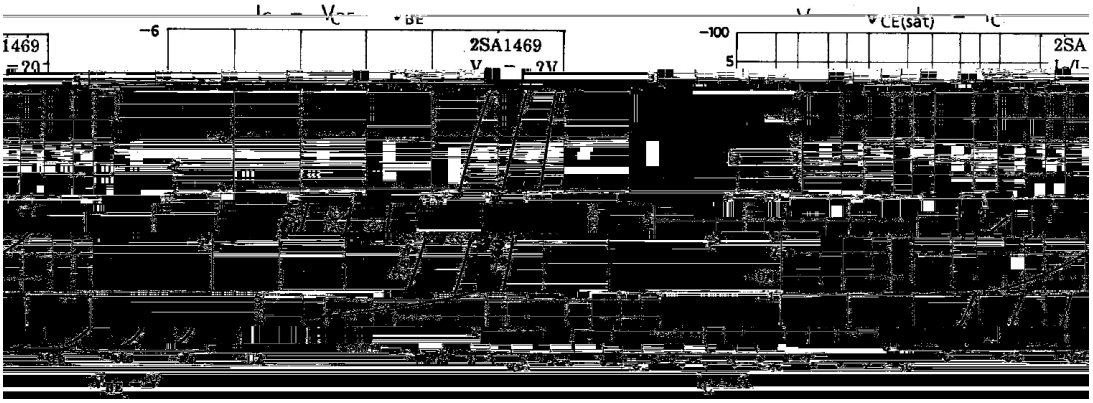
/ Absolute Maximum Ratings(Ta=25)

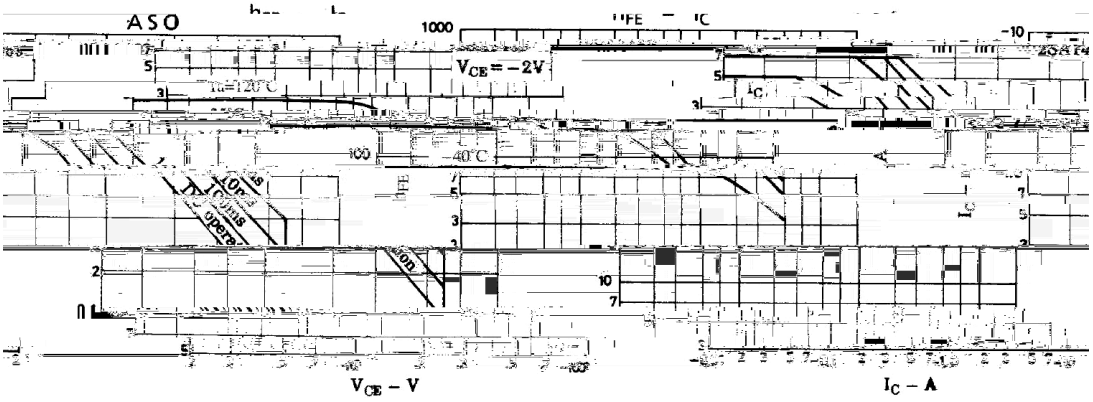
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-80	V
Collector to Emitter Voltage	V_{CEO}	-60	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-5.0	A
Collector Current – Continuous(Pulse)	I_{CP}	-7.0	A
Collector Power Dissipation	P_C	2.0	W
Collector Power Dissipation	P_C(Tc=25)	20	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

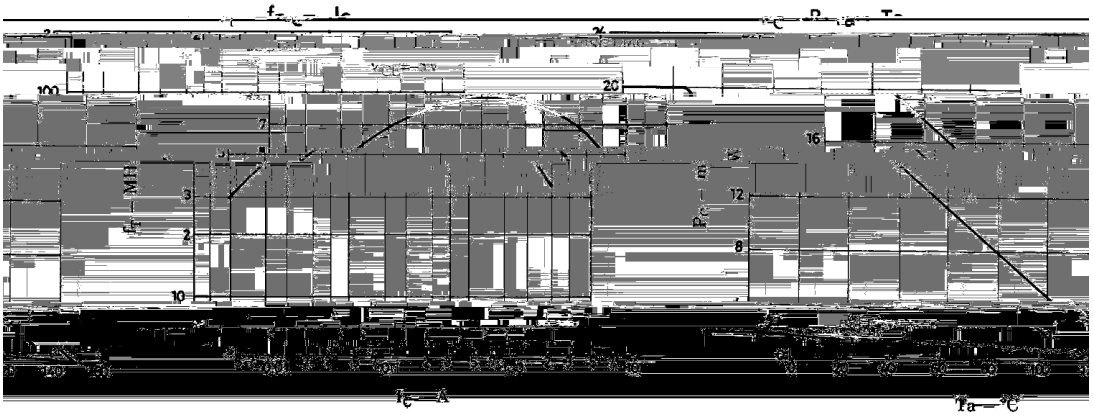
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-1.0mA I_E=0	-80			V
Collector to Base Breakdown Voltage	V_{CEO}	I_C=-1.0mA I_B=0	-60			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=-1.0mA I_C=0	-5.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-40V I_E=0			-0.1	mA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-4.0V I_C=0			-0.1	mA
DC Current Gain	h_{FE}	V_{CE}=-2.0V I_C=-1.0A	70		280	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-2.5A I_B=-0.125A			-0.4	V
Transition Frequency	f_T	V_{CE}=-5.0V I_C=-1.0A		100		MHz
Turn-On Time	t_{on}	$20I_{B1}$=-$20I_{B2}$=I_C=2A		0.1		s
Storage Time	t_{stg}			0.5		
Fall Time	t_f			0.1		

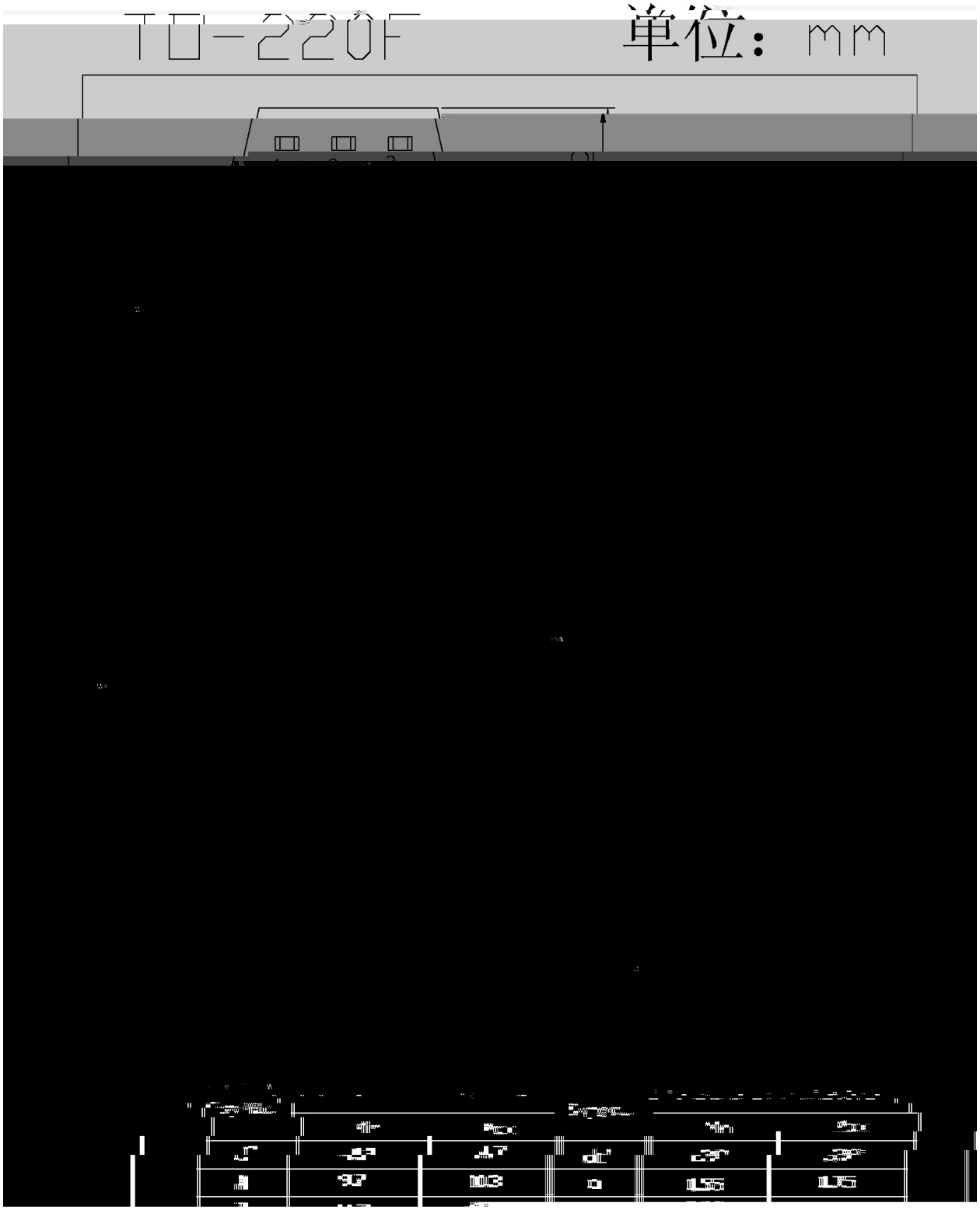
/ Electrical Characteristic Curve







/ Package Dimensions



( ) / Temperature Profile for Dip Soldering(Pb-Free)



	Note:
1 25 150 60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2 255±5 5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.
3 2 10 /sec.	3. Cooling Speed: 2~10 /sec.

5 • ỗ B I 255±